



ZTX792A

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

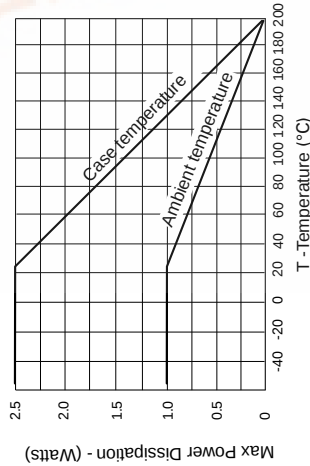
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f _T	100			MHz	I _C =50mA, V _{CE} =5V f=50MHz
Input Capacitance	C _{ibo}		225		pF	V _{EB} =-0.5V, f=1MHz
Output Capacitance	C _{obo}		22		pF	V _{CB} =-10V, f=1MHz
Switching Times	t _{on}	35			ns	I _C =-500mA, I _{B1} =50mA
	t _{off}	750			ns	I _{B2} =-50mA, V _{CC} =-10V

Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

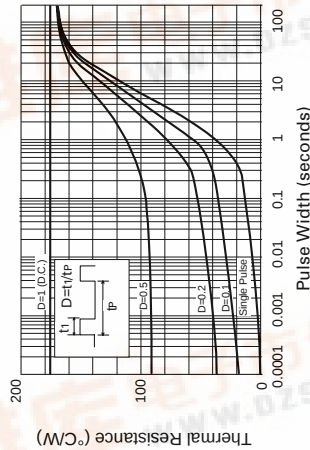
HERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient, Junction to Ambient, Junction to Case	R _{th(j-amb)1}	175	°CW
	R _{th(j-amb)2} †	116	°CW
	R _{th(j-case)}	70	°CW

Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



Derating curve



Maximum transient thermal impedance

PNP SILICON PLANAR MEDIUM POWER
HIGH GAIN TRANSISTOR

ISSUE 2 - APRIL 94

FEATURES

- * 70 Volt V_{CEO}
 - * Gain of 400 at I_C=3 Amps
 - * Very low saturation voltage
- APPLICATIONS
- * Darlington replacement
 - * Flash gun converters
 - * Battery powered circuits
 - * Motor drivers

ABSOLUTE MAXIMUM RATINGS.

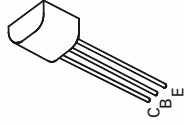
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-75	V
Collector-Emitter Voltage	V _{CEO}	-70	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-4	A
Continuous Collector Current	I _C	-2	A
Practical Power Dissipation*	P _{totp}	1.5	W
Power Dissipation at T _{amb} =25°C derate above 25°C	P _{tot}	1	W
		5.7	mW/°C
Operating and Storage Temperature Range	T _J ; T _{stg}	-55 to +200	°C

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-75			V	I _C =-100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-70			V	I _C =-10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5			V	I _E =-100μA
Collector Cut-Off Current	I _{CBO}			-0.1	μA	V _{CB} =-40V
Emitter Cut-Off Current	I _{EBO}			-0.1	μA	V _{EB} =-4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.45	V	I _C =-500mA, I _B =-5mA*
				-0.5	V	I _C =-1A, I _B =-25mA*
				-0.5	V	I _C =-2A, I _B =-200mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			-0.95	V	I _C =-1A, I _B =-25mA*
Base-Emitter Turn-On Voltage	V _{BE(on)}		-0.75		V	I _C =-1A, V _{CE} =-2V*
Static Forward Current Transfer	h _{FE}	300		800		I _C =-10mA, V _{CE} =-2V*
		250				I _C =-500mA, V _{CE} =-2V*
		200				I _C =-1A, V _{CE} =-2V*

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E-Line
TO92 Compatible

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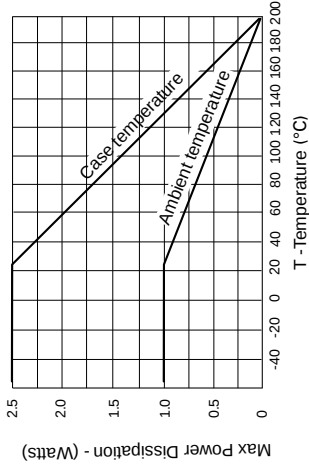
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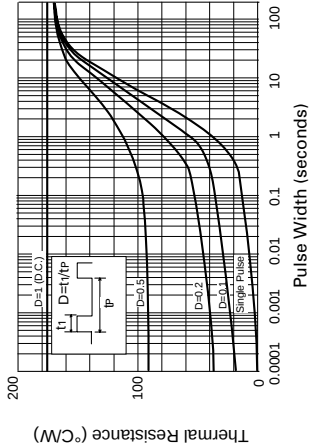
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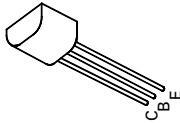
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TYPICAL CHARACTERISTICS

